



P-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	-20V
I_D	-0.65A
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	850 mohm
$R_{DS(ON)}$ (at $V_{GS}=-2.5V$)	1200 mohm
$R_{DS(ON)}$ (at $V_{GS}=-1.8V$)	2000



Typical Performance Characteristics

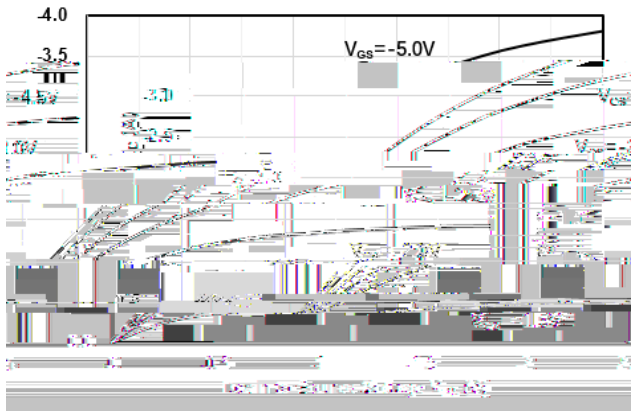


Figure1. Output Characteristics

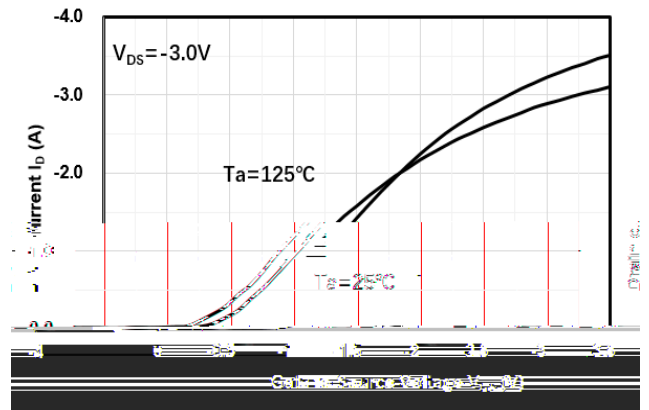


Figure2. Transfer Characteristics

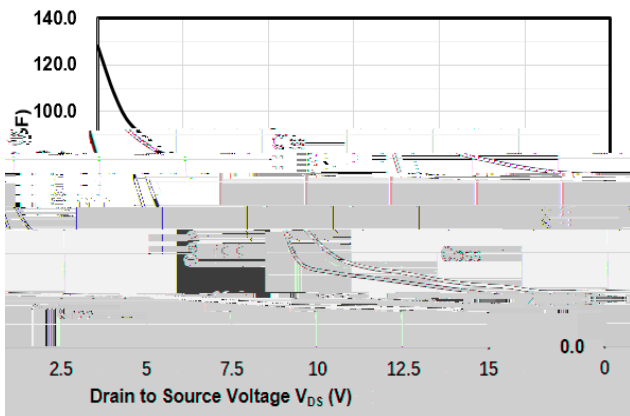


Figure3. Capacitance Characteristics

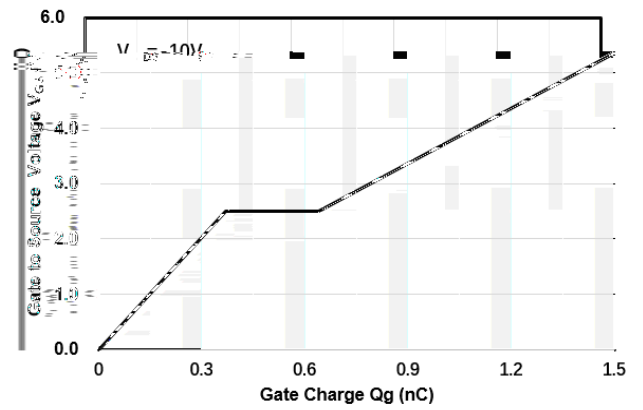


Figure4. Gate Charge

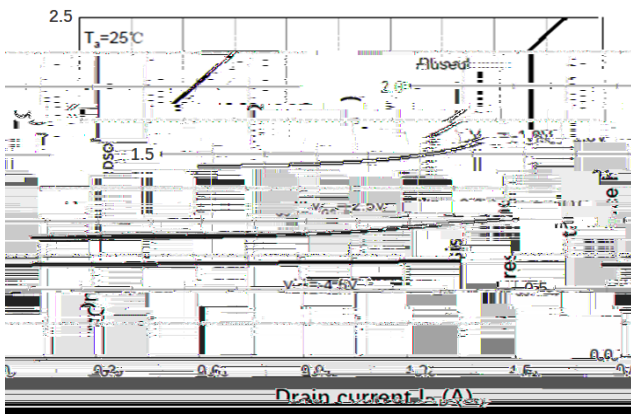


Figure5. Drain-Source on Resistance

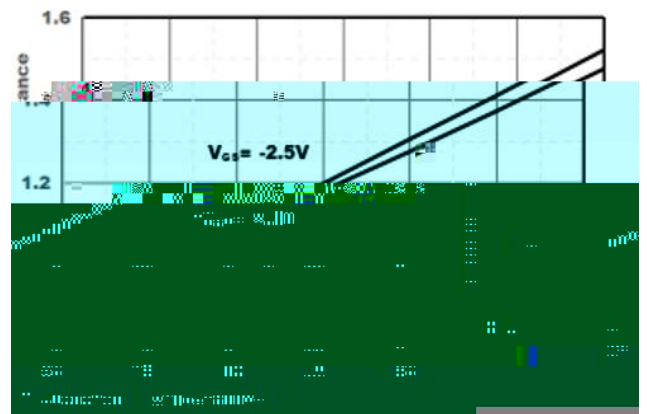


Figure6. Drain-Source on Resistance

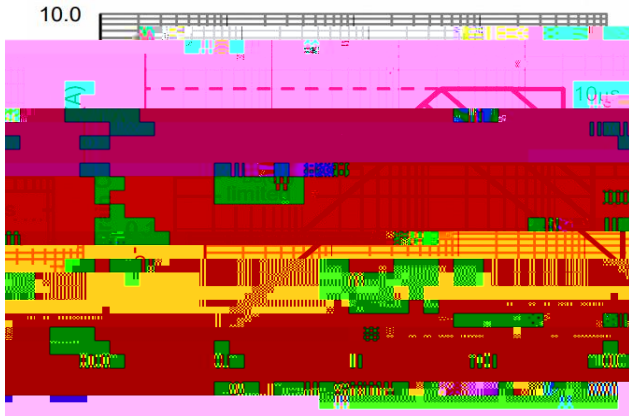


Figure7. Safe Operation Area

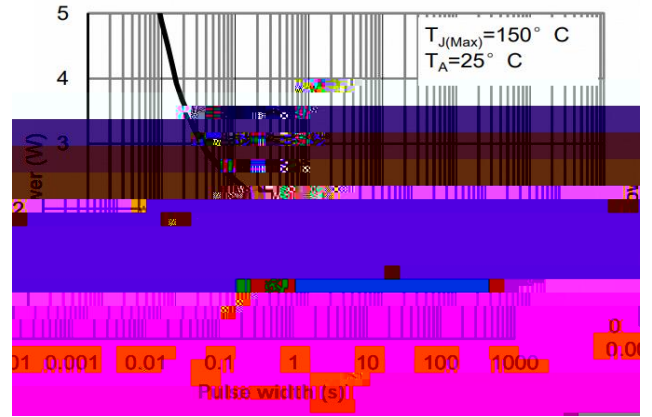


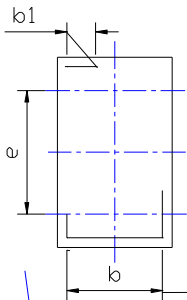
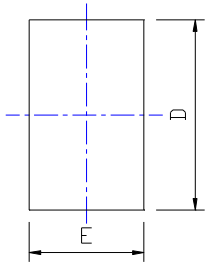
Figure8. Pulse Power Rating Junction-to Ambient



Figure9. Normalized Maximum Transient Thermal Impedance



DFN1006-3L Package information



UNIT mm

